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	Application No.	Applicant(s)	AL
Aladia a a C. Allanca L. 1156	10/712,017	WATANABE ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Michael Trinh	2822	
The MAILING DATE of this communication a All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL- NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATEN of the Office or upon petition by the applicant. See 37 CFR 1.	SIS (OR REMAINS) CLOSED in 85) or other appropriate commur TRIGHTS. This application is su	this application. If not included nication will be mailed in due cour	rse. THIS
1. This communication is responsive to <u>Amendment filed</u>	<u>June 16, 2005</u> .		
2. The allowed claim(s) is/are 1-3 and 5-13.		•	
3. A The drawings filed on 14 November 2003 are accepted	by the Examiner.		
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority a)  All b)  Some* c)  None of the: <ol> <li>Certified copies of the priority documents heteroidal copies of the priority documents heteroidal copies of the priority documents heteroidal copies of the priority linternational Bureau (PCT Rule 17.2(a)).</li> </ol> </li> <li>* Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DAT noted below. Failure to timely comply will result in ABANDO </li> </ul>	nave been received.  nave been received in Application  of documents have been received  fe" of this communication to file a	No in this national stage application	
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5. A SUBSTITUTE OATH OR DECLARATION must be su	ubmitted. Note the attached EXAN	MINER'S AMENDMENT or NOTIC	CE OF
INFORMAL PATENT APPLICATION (PTO-152) which  6. CORRECTED DRAWINGS (as "replacement sheets") r  (a) including changes required by the Notice of Draftsp  1) hereto or 2) to Paper No./Mail Date	must be submitted.  person's Patent Drawing Review	( PTO-948) attached	
(b) ☐ including changes required by the attached Examir Paper No./Mail Date  Identifying indicia such as the application number (see 37 CF	R 1.84(c)) should be written on the	drawings in the front (not the bac)	k) of
<ul> <li>each sheet. Replacement sheet(s) should be labeled as such</li> <li>DEPOSIT OF and/or INFORMATION about the deattached Examiner's comment regarding REQUIREMENT</li> </ul>	eposit of BIOLOGICAL MATER	RIAL must be submitted. Note	the
<ul> <li>Attachment(s)</li> <li>1. ☐ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-94)</li> <li>3. ☐ Information Disclosure Statements (PTO-1449 or PTO/S Paper No./Mail Date</li></ul>	.8) 6. ☐ Interview Sun Paper No./M 5B/08), 7. ☐ Examiner's A	ail Date mendment/Comment tatement of Reasons for Allowand	,
		Michael Trinh Primary Examiner	r

Art Unit: 2822

## **DETAILED ACTION**

\*\*\* This office action is in response to Applicant's Amendment filed June 16, 2005. Claims 1-3,5-13 are pending.

## Allowable Subject Matter

- 1. Claims 1-3 and 5-13 are allowed.
- 2. The following is a statement of reasons for the indication of allowable subject matter:

Applicant's amendment and convincing remarks filed June 16, 2005 have overcome the rejections of record. The references of record including Sachiko (JP-11-168052), Takamitsu (JP-2001-274062), Koji (JP-2002-164302), etc., alone or in combination, do not anticipatively disclose each and every aspect of the method for forming a pattern, or fairly make a prima facie obvious case of the claimed method, in combination with other processing claimed limitations as recited in base claims, the inclusion of, such as in claim 1, forming a resist film on top of the workpiece film formed on a substrate, the resist film having a first glass transition temperature; disposing a mask and irradiating the resist film with a first energy beam through the mask; forming a first resist pattern by developing the resist film after applying the first energy beam; irradiating the first resist pattern with a second energy beam after removal of the mask, to thereby effect a crosslinking reaction in the first resist pattern, and so that the first resist pattern is caused to have a second glass transition temperature that is higher than the first glass transition temperature; forming a second resist pattern smaller than the first resist pattern by subjecting the first resist pattern to heat treatment after applying the second energy beam, the heat treatment being performed at a temperature that is higher than the first glass transition temperature; and patterning the workpiece film by use of the second resist pattern as a mask.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 8:30 Am to 5:00 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone numbers for the organization where this application proceeding is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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Michael Trinh Primary Examiner